

*A' Concl.*

62. A method for dynamic correction of scanning energy in the projection exposure system of claim 59, comprising the steps of:  
measuring a distribution of scanning energy  $SE_{wafer}(x_{wafer})$  in  
said second imaging plane;  
comparing said measured distribution of scanning energy  
 $SE_{wafer}(x_{wafer})$  to a predetermined distribution of scanning  
energy  $SE_{Standard}(x_{wafer})$ ;

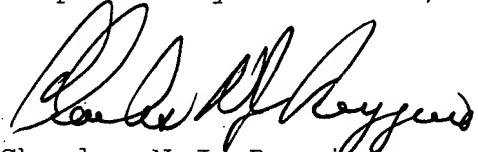
controlling an actuator to modify said field lens group to  
minimize a difference between said measured distribution  
of scanning energy  $SE_{wafer}(x_{wafer})$  and said predetermined  
distribution of scanning energy  $SE_{Standard}(x_{wafer})$ .

*32*  
63. A method of producing microstructured devices by  
lithography, comprising the step of using the projection exposure  
apparatus of claim 59.--

REMARKS

New claims 31 through 63 are added to protect properly the full scope of the invention.

Respectfully submitted,



Charles N.J. Ruggiero  
Reg. No. 28,468  
Attorney for the Applicant  
Ohlandt, Greeley, Ruggiero  
& Perle, L.L.P.  
One Landmark Square, 9th Floor  
Stamford, CT 06901-2682  
Tel: (203) 327-4500  
Fax: (203) 327-6401

February 25, 2000

Date